

## **KSC5021F**

### High Voltage and High Reliability

- High Speed Switching :  $t_F = 0.1 \mu s(Typ.)$ WWW.DZSC.COM
- Wide SOA



2.Collector 3.Emitter

### **NPN Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	800	V
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current (DC)	5	Α
I <sub>CP</sub>	Collector Current (Pulse)	10	Α
I <sub>B</sub>	Base Current	2	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	40	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 1 \text{mA}, I_E = 0$	800			V
BV <sub>CEO</sub>	Collector-Emitter Sustaining Voltage	$I_C = 5 \text{mA}, I_B = 0$	500			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V <sub>CEX</sub> (sus)	Collector-Emitter Sustaining Voltage	$I_C = 2.5A, I_{B1} = -I_{B2} = 1A$ L = 1mH, Clamped	500			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 500V, I_{E} = 0$	100		10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h <sub>FE1</sub> h <sub>FE2</sub>	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.6A$ $V_{CE} = 5V, I_{C} = 3A$	15 8	M AN AN	50	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$			1.5	V
C <sub>ob</sub>	Output Capacitance	$V_{CB} = 10V, I_E = 0, f = 1MHz$		80		pF
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.6A$		15		MHz
ton	Turn On Time	V <sub>CC</sub> = 200V			0.5	μs
t <sub>STG</sub>	Storage Time	$I_C = 5I_{B1} = -2.5I_{B2} = 4A$			3	μs
t <sub>F</sub>	Fall Time	$R_L = 50\Omega$			0.3	μs

## **h**<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE1</sub>	15 ~ 30	20 ~ 40	30 ~ 50

## **Typical Characteristics**

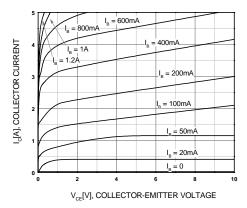


Figure 1. Static Characteristic

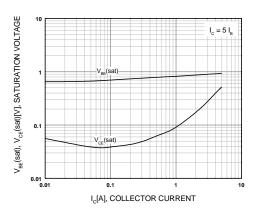


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

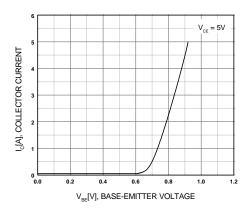


Figure 5. Base-Emitter On Voltage

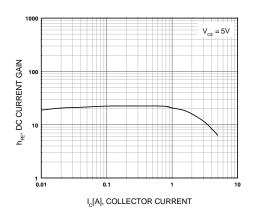


Figure 2. DC current Gain

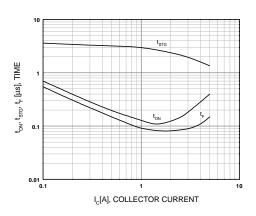


Figure 4. Switching Time

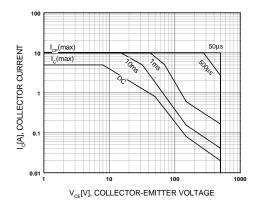


Figure 6. Safe Operating Area

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# Typical Characteristics (Continued)

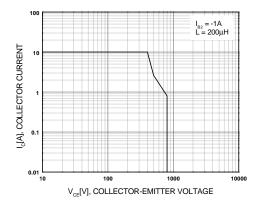


Figure 7. Reverse Bias Safe Operating Area

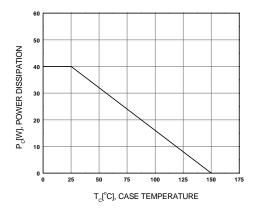
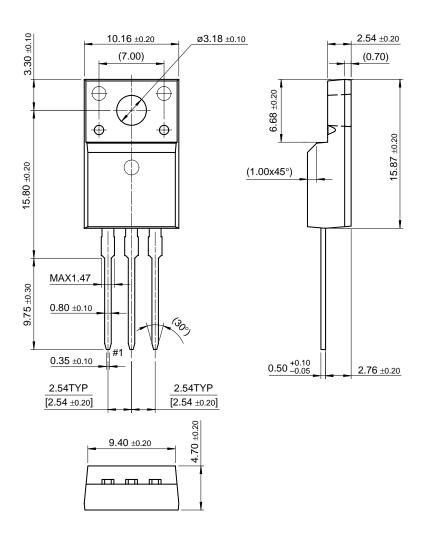


Figure 8. Power Derating

# **Package Dimensions**

# TO-220F



Dimensions in Millimeters

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$CROSSVOLT^{TM}$	FRFET™	MicroPak™	QFET™	SuperSOT™-8
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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E2CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™ _
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Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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